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QHE, magnetoresistance and disordered transport on 2D mesoscopic plaquettes.

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Abstract

The transport properties of a rectangular mesoscopic plaquette in the presence of a perpendicular magnetic field are studied in a tight-binding model with randomly distributed traps. The longitudinal and Hall resistances are calculted in the four-probe Landauer-Büttiker formalism which accounts automatically both for the quantum coherence and the trapping-induced localization. The localized character of eigenvectors and the specific aspect of the density of states at a given magnetic flux are correlated with the behaviour of the mentioned resistances as function of the Fermi energy. The Hall insulator and quantum Hall regimes are evidentiated. The dependence on magnetic field of the configurational averages of the longitudinal and Halll resistance is studied in a purely quantum-mechanical approach. Both negative and positive magnetoresistances are found.

72.90, 73.23

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The electronic mesoscopic transport on a plaquette in the presence of an external random atractive potential (traps) and of a perpendicular magnetic field exhibits a number of interesting properties. They are due to the modifications induced by traps in the Hofstadter energy spectrum and to the changes in the nature of the eigenstates. For a clean, infinite plaquette the spectrum consists of alternating bands and magnetic gaps described by the Hofstadter butterfly. In a finite plaquette edge states start filling the gaps (thus turning them into quasi-gaps). The presence of traps, beside shifting the spectrum downwards, gives rise to localized states at its bottom. When the traps are sufficiently deep and rare, the localized levels are well separated by a spectral gap from the rest of the spectrum which is still reminiscent of the former butterfly. This case turns out to be the most interesting one since band-, localized-, and edge-states are encountered simultaneously with true and pseudo-gaps.

The transport properties of the plaquette should show at least two distinct behaviours: a high resistive one, for energies corresponding to either localized states or the gap, and the quantum Hall behaviour, when the transport takes place along the edge states in the pseudo-gap. It is hard to say, a priori, how the Hall resistance will be looking like in the first case and also what the effect of traps on the edge-state transport will be. These aspects will be discussed below.

In the present frame, new arguments can be obtained concerning the problem of interference effect on the conduction phenomena in weak magnetic field and strongly localized regime. Unlike other approaches [1-3] we are able to take completely into consideration the quantum coherence (the backscattering is included) and to describe the Hall resistance,too. In the mentioned papers, the magnetic field dependence of the transition probabilities between two quantum states appears exclusively through the resonance integral. In finite samples, the resonance integral shows strong mesoscopic oscillations as the magnetic field increases from zero, however a configurational average will have a smooth dependence. Performing a 'logarithmic average' over all directed paths (contained in a cigar- shaped region between two states), Ngyen,Shklovskii and Spivak [1] get a negative magnetoresistance, linear in magnetic field. The same result is obtained by Schirmacher in an effective medium approximation [2], but, using again EMA, Böttger et al.[3] get a quadratic behaviour. Using another way of averaging, Entin-Wohlman at al.[4] obtain a quadratic dependence in the low field limit, both negative or positive, depending on the resistivity of the system. The experiments show two types of behaviour,too [5].

The longitudinal and Hall resistances of a plaquette with four attached leads are calculated at zero temperature using the Landauer-Büttiker formalism and a tight-binding Hamiltonian. The conductances $g_{\alpha\beta}$ between two leads denoted by α and β are given by the scattering amplitude between the leads and the resistances R_L (longitudinal) and R_H (Hall) can be expressed in terms of $g_{\alpha\beta}$ [6]. The details can be found in [7] and a similar approach was used by Gagel and Maschke in Ref.8. Since in 2D the strong localization cannot be induced by disorder, we shall induce it by trapping. In the tight-binding model, the traps are simulated by negative energies assigned to some sites in the diagonal term of the Hamiltonian describing the plaquette :

$$H^S = \sum_{n=1}^{N} \sum_{m=1}^{M} [\, \epsilon_{nm} |n,m\rangle\langle n,m| + e^{i2\pi\phi m} |n,m\rangle\langle n+1,m| + |n,m\rangle\langle n,m+1| + h.c. \,] \,, \qquad (1)$$

where $|n,m\rangle$ is a set of orthonormal states localized at the sites (n,m), and ϕ is the magnetic flux through the unit cell (measured in quantum flux units.). In Eq.(1) $\epsilon_{nm} = 0$ except for the trap sites which are chosen at random with concentration c. The hopping term is taken equal to 1 (up to the magnetic phase) and this specifies the energy scale.

The integrated density of states (IDOS) of this Hamiltonian is shown in Fig.1 The black regions represent the regions where the eigenvectors are grouped together forming bands. In the grey regions, IDOS increases slowly with the energy, the eigenvalues are rare and the corresponding eigenvectors are localized on the edges. It can be checked that below the lowest band there are few eigenvalues , the corresponding vectors being strongly localized on the traps. Further information can be obtained from the degree of occupation of the traps, i.e. $\sum_i |\Psi_i|^2, (i \in traps)$. This quantity is shown for different energies in Fig.2. It takes high values for localized states as it should, however small maxima appear also in pseudo-gaps due to the admixture of impurity states localized in the pseudo-gaps with the quasi-continuum of the edge states.

At the bottom of the spectrum, as far as the energy runs through the domain of localized states, the Hall resistance shows oscillations. However, once entering the gap a Hall insulator behaviour is installed. This is characterized by extremely high values of R_L, but also by small values and a smooth dependence on energy of R_H . The Hall insulator regime is explained easily along with the argument outlined in [9]. Essentially it arises from the fact that the propagator between lead contact points is exponentially small $g_{\alpha,\beta} \sim \lambda^2$ where $\lambda \propto \; exp(-\xi d_{\alpha\beta})$ (ξ = the inverse decay length, $d_{\alpha\beta}$ =distance between contacts). The leading λ^2-term of the conductance matrix is symmetric and the antisymmetric part starts with the next-to-leading λ^4-term. One is lead to the conclusion that the inverse of $g_{\alpha\beta}$ (which gives the resistances) contains a singular λ^{-2} part, which is symmetric. Therefore R_H ,being an antisymmetric quantity, remains non-singular.

The first QH plateau appears above the Hall insulator domain. In the QH regime there is a competition between the localization at the edges due to the magnetic field and the localization on the trapping sites due to the electrostatic atractive potential as discussed above. In spite of this one has to note that the plateaus in Fig.3 are not affected by this change in the nature of the eigenfunction. Of course, at high trap concentration, the localization on traps is much stronger, the pseudo-gaps and the plateaus disappear at the inferior part of the spectrum, which is more influenced by the trapping potential, however they may be maintained at higher energies.

The average values of R_L and R_H over an ensemble of mesoscopic plaquettes may give hints on the expected macroscopic behaviour of these entities. The macroscopic condition of self-averaging is difficult to be reached technically because it requires a large plaquette. For the dimension we used (64x10 atomic distances) the distribution function of R_L is broad and consequently $\langle R_L \rangle \neq \langle 1/R_L \rangle^{-1}$. Nevertheless the averages $\langle R_L \rangle, \langle logR_L \rangle$ and $\langle R_H \rangle$ show a smooth dependene on the magnetic flux and this is true for the second moment, too. These average values have been calculated at two different energies, corresponding to the localized and band regime. In the localized case, $\langle R_L \rangle$ and $\langle log R_L \rangle$ show negative magnetoresistance with a B^2-dependence at low magnetic field B as in [3,4]. This dependence is weakened gradually with increasing B, ending up with the change of slope at higher fields (see Fig.4). On the contrary, in the band regime (see Fig.5), we found a linear positive magnetoresistance at low fields, followed by a change to negative behaviour at higher fields. In the present approach, one realizes why in the strongly localized regime (hopping) the magnetoresistance should be quadratic. This stems from the dominance (see above) of the symmetric part of $g_{\alpha\beta}$,which is an even function of ϕ. No such arguments hold in the band regime. In what concerns the Hall resistance, it starts linearly, but changes eventually the slope and even the sign.

In conclusion, the mesoscopic plaquette with random traps allows the study of the transport properties both in the localized and quantum Hall regime. In the range of localized states, one observes the Hall insulator behaviour. At higher energies, QH plateaus exist even in the presence of traps, in spite of the fact that the edge states get some localization on the trapping sites. For ensemble-averaged values, this purely quantum-mechanical approach confirms the negative magnetoresistance (starting with a quadratic dependence on the magnetic field) in the case of strong localization. The Hall resistance could also be calculated, but a deeper scrutiny of both localized and band case is necessary.

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FIGURES

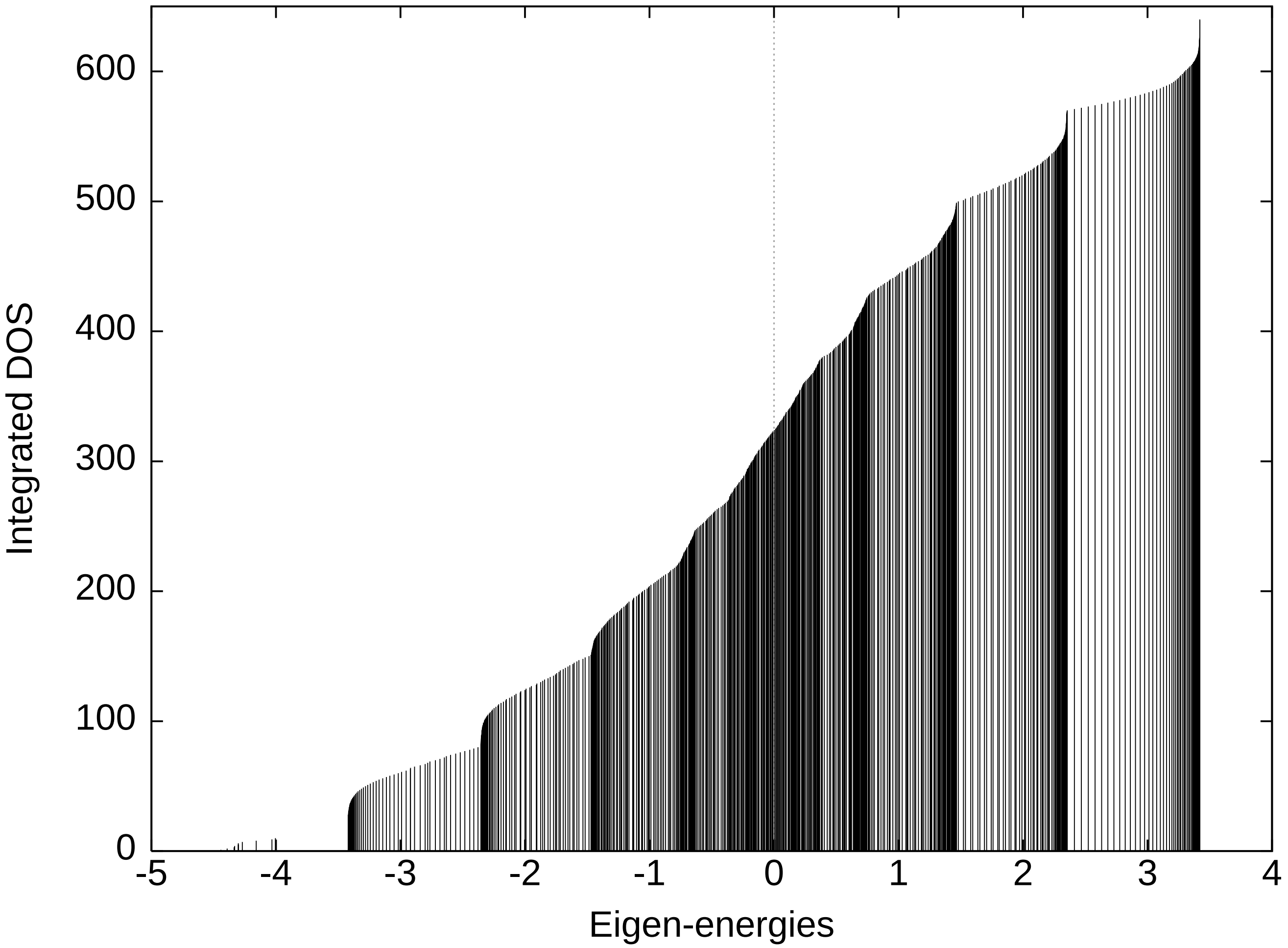
FIG. 1. The integrated density of states of a disordered plaquette ($\phi = 0.1,\ E_{trap} = -3.0,\ c = 1/64$).

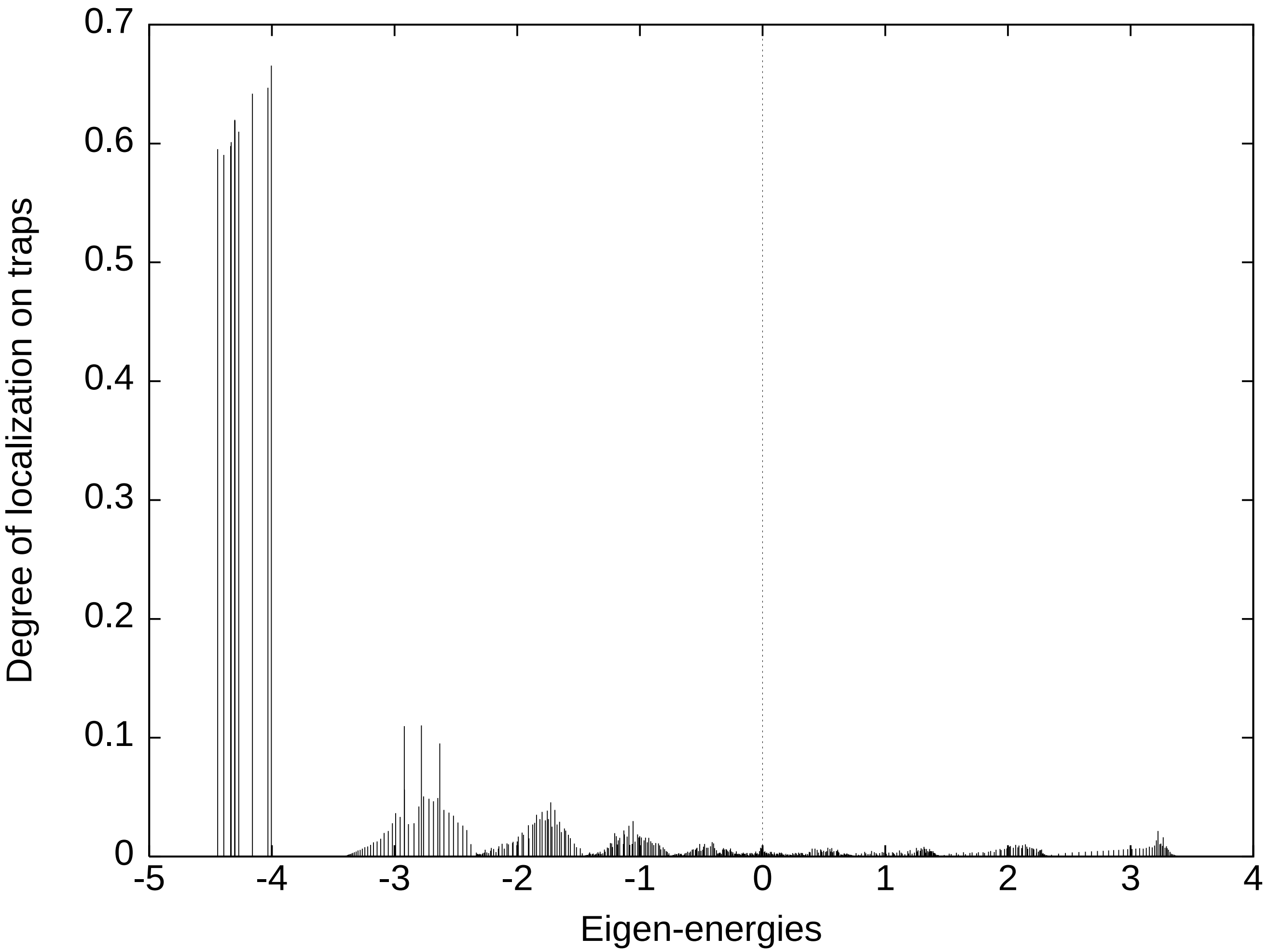
FIG. 2. The degree of localization on traps $\sum_i |\Psi_i|^2 (i \in traps)$ as function of energy for the same plaquette as in Fig.1.

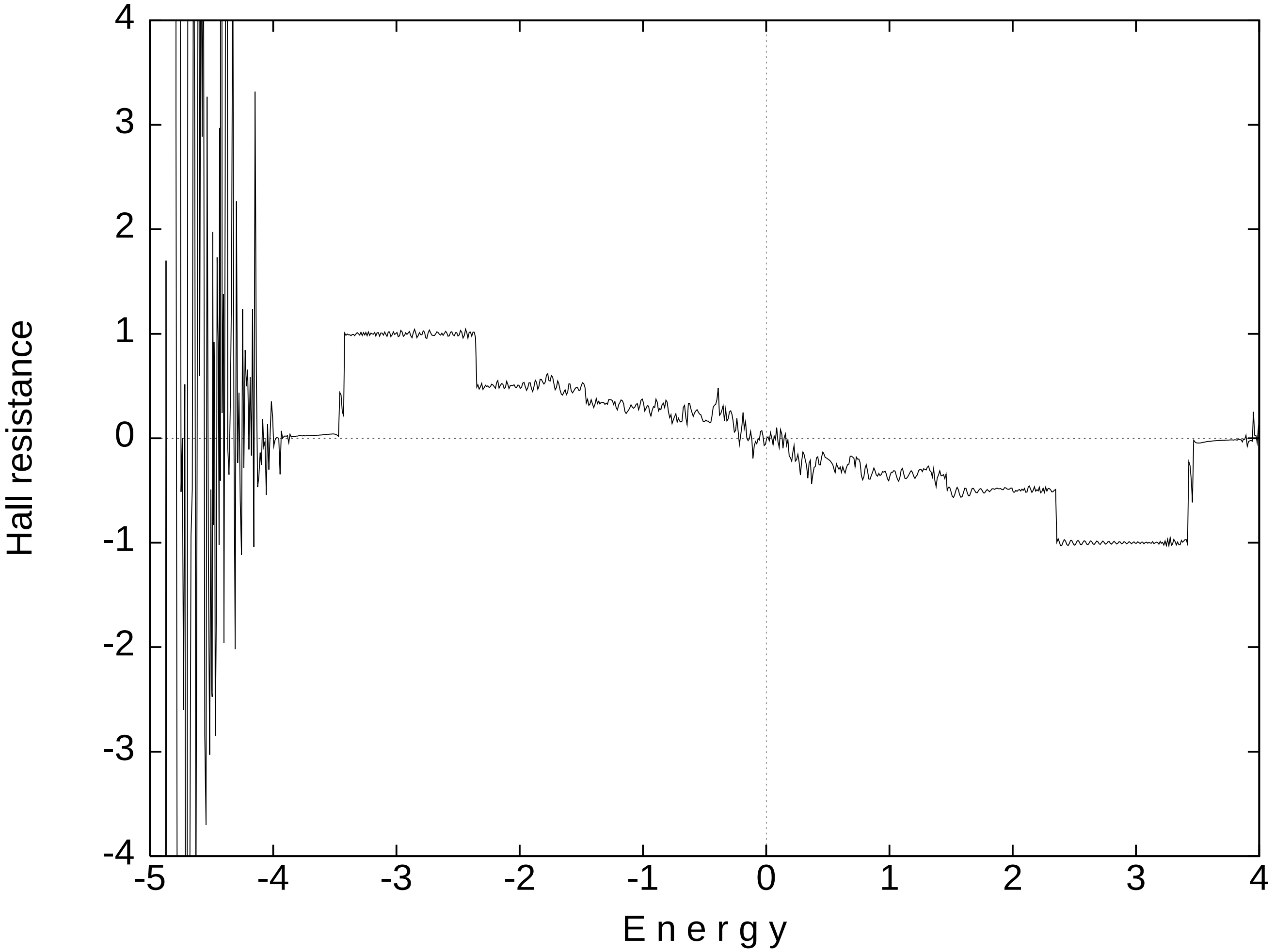
FIG. 3. The Hall resistance as function of energy for the same plaquette as in Fig.1.

FIG. 4. The ensembe averages $\langle R_l \rangle$ and $\langle R_H \rangle$ as function of the magnetic flux in the high resistance regime ($E_{Fermi} = -4.2,\ E_{trap} = -3.0,\ c = 1/64$)

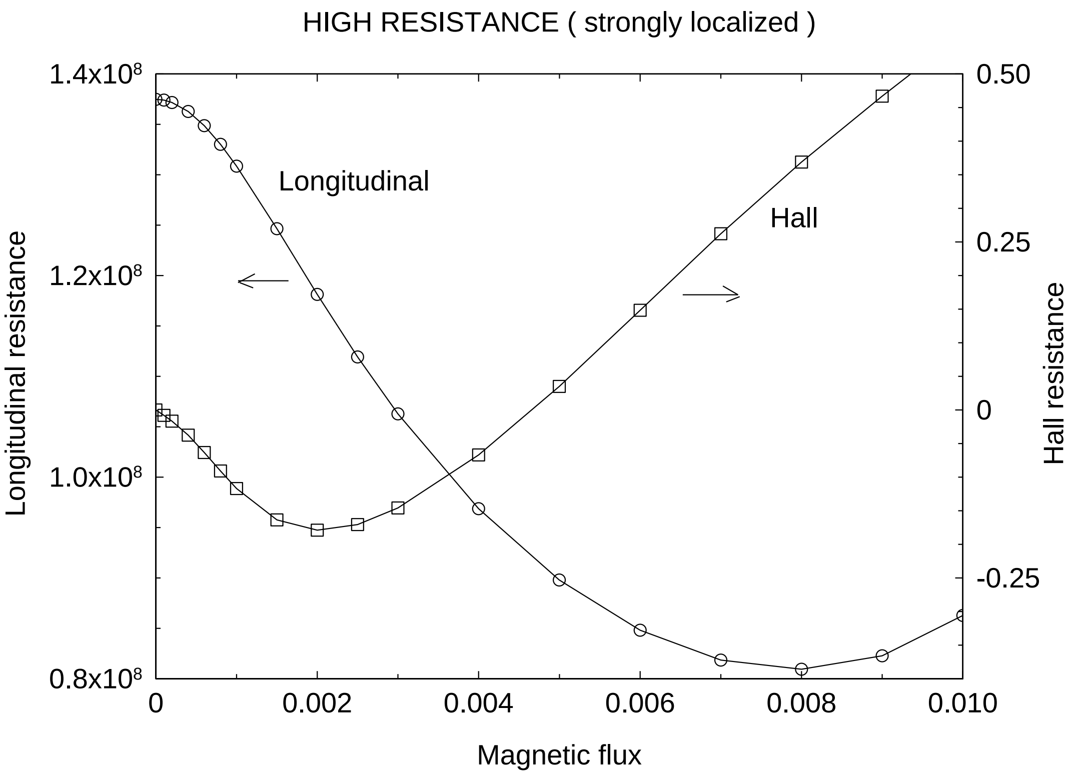
FIG. 5. The same as in Fig.4 in the low resistance regime ($E_{Fermi} = -0.5$)


Integrated DOS
Eigen-energies
0
100
200
300
400
500
600
-5
-4
-3
-2
-1
0
1
2
3
4

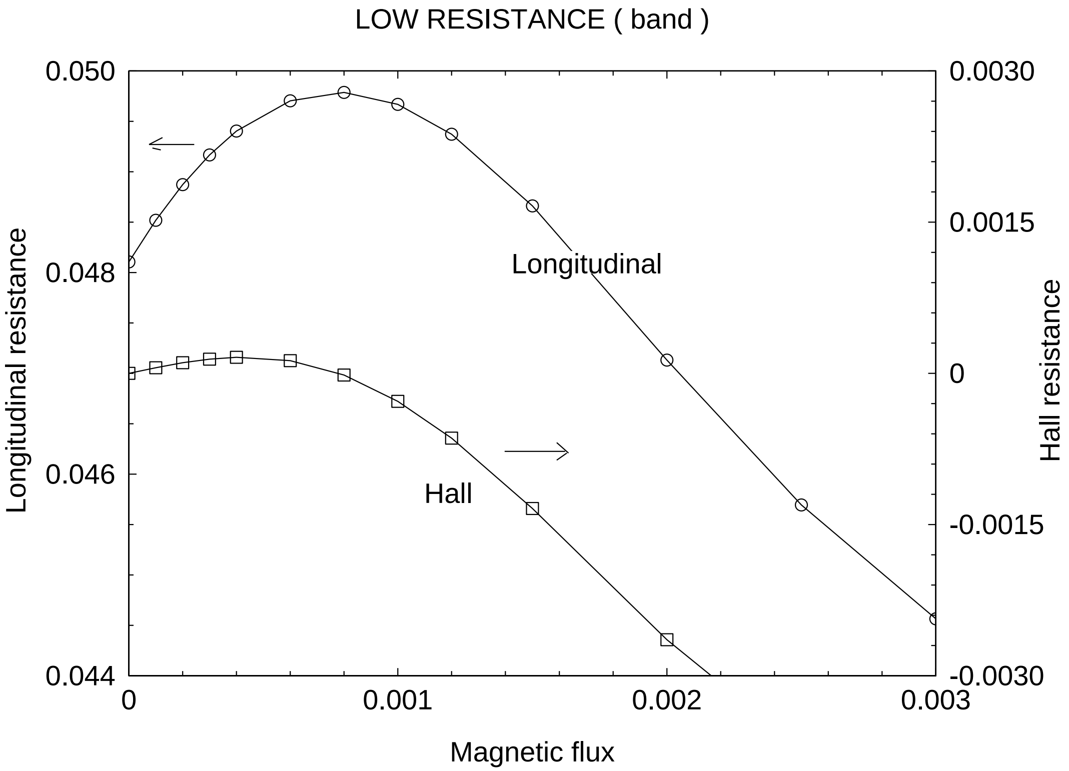

0.7
0.6
0.5
0.4
0.3
0.2
0.1
0
Degree of localization on traps
-5
-4
-3
-2
-1
0
1
2
3
4
Eigen-energies



Hall resistance
4
3
2
1
0
-1
-2
-3
-4
-5
-4
-3
-2
-1
0
1
2
3
4
Energy



HIGH RESISTANCE (strongly localized)


LOW RESISTANCE (band)
0.050
0.048
0.046
0.044
0.0030
0.0015
0
-0.0015
-0.0030
0
0.001
0.002
0.003
Longitudinal resistance
Hall resistance
Magnetic flux
Longitudinal
Hall